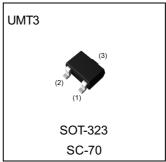


Medium power transistor (-60V, -0.5A)

Parameter	Value
V _{CEO}	-60V
I _C	-0.5A

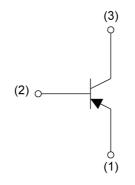
Outline



Features

- 1)High speed switching. (Tf:Typ.:60ns at I_C=-500mA)
- 2)Low saturation voltage, typically (Typ.:-150mV at I_C=-100mA, I_B=-10mA)
- 3)Strong discharge power for inductive load and capacitance load.
- 4)Complements the 2SC5876

•Inner circuit



- (1) Emitter
- (2) Base
- (3) Collector

Application

SMALL SIGNAL LOW FREQUENCY AMPLIFIER, HIGH SPEED SWITCHING

Packaging specifications

Part No.	Package	Package size	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit.(pcs)	Marking
2SA2088	UMT3	2021	T106	180	8	3000	VM

• Absolute maximum ratings ($T_a = 25$ °C)

Parameter	Symbol	Values	Unit
Collector-base voltage	V_{CBO}	-60	V
Collector-emitter voltage	V _{CEO}	-60	V
Emitter-base voltage	V _{EBO}	-6	V
Calle ster arrange	I _C	-0.5	Α
Collector current	I _{CP} *1	-1.0	Α
Power dissipation	P _D *2	200	mW
Junction temperature	Tj	150	°C
Range of storage temperature	T _{stg}	-55 to +150	ဇင

• Electrical characteristics $(T_a = 25^{\circ}C)$

Parameter	Cumb al	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Collector-base breakdown voltage	BV _{CBO}	I _C = -100μA	-60	-	-	V
Collector-emitter breakdown voltage	BV _{CEO}	I _C = -1mA	-60	ı	ı	V
Emitter-base breakdown voltage	BV _{EBO}	I _E = -100μA	-6	1	-	V
Collector cut-off current	I _{CBO}	V _{CB} = -40V	-	-	-1.0	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -4V	-	-	-1.0	μA
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -100mA, I _B = -10mA	-	-150	-500	mV
DC current gain	h _{FE}	$V_{CE} = -2V, I_{C} = -50 \text{mA}$	120	-	270	-
Transition frequency	f _T *3	$V_{CE} = -10V, I_{E} = 100 \text{mA},$ f = 100MHz	-	400	-	MHz
Output capacitance	C _{ob}	V_{CB} = -10V, I_E = 0mA, f = 1MHz	-	10	-	pF
Turn-On time	t _{on}	I _C = -500mA, I _{B1} = -50mA,	-	35	1	ns
Storage time	t _{stg}	$I_{B2} = 50 \text{mA},$ $V_{CC} \simeq -25 \text{V},$	-	100	-	ns
Fall time	t _f	$R_L = 50\Omega$ See test circuit	-	60	-	ns

hFE values are calssified as follows:

rank	Q	-	-	-	-
hFE	120-270	-	-	-	-

^{*1} Pw=10ms, Single pulse

^{*2} Each terminal mounted on a reference land.

^{*3} Pulsed

● Electrical characteristic curves(T_a = 25°C)

Fig.1 Ground Emitter Propagation

Characteristics

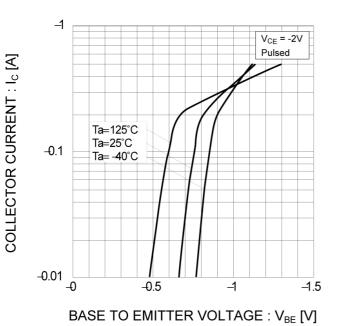
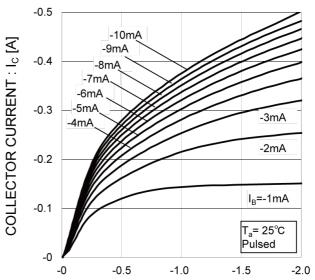


Fig.2 Typical Output Characteristics



COLLECTOR TO EMITTER VOLTAGE: VCE [V]

Fig.3 DC Current Gain vs. Collector Current (I)

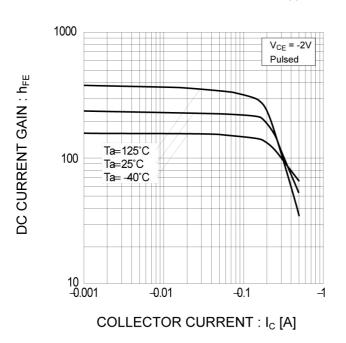
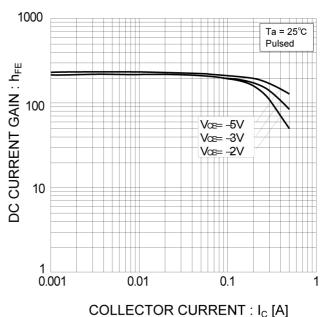


Fig.4 DC Current Gain vs. Collector Current (II)



● Electrical characteristic curves(T_a = 25°C)

Fig.5 Collector-Emitter Saturation Voltage vs. Collector Current (I)

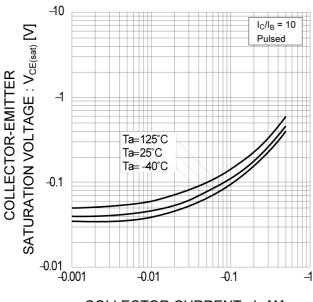
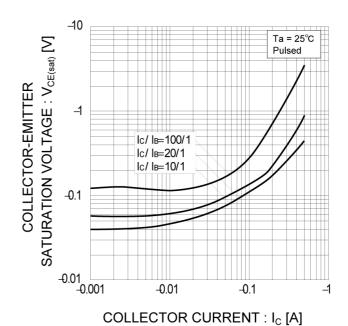


Fig.6 Collector-Emitter Saturation
Voltage vs. Collector Current (II)



COLLECTOR CURRENT: Ic [A]

Fig.7 Base-Emitter Saturation Voltage vs. Collector Current

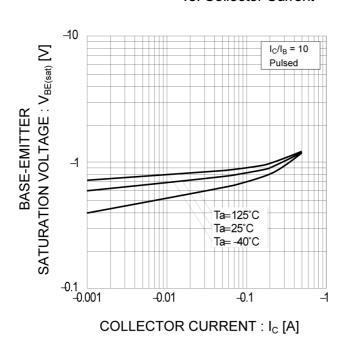
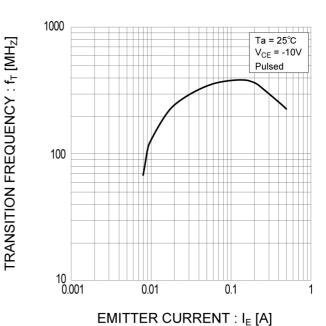


Fig.8 Gain Bandwidth Product vs.

Emitter Current

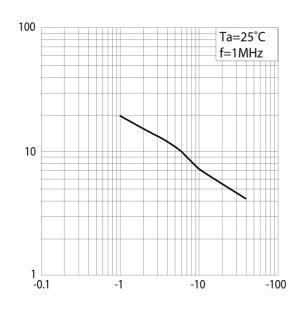


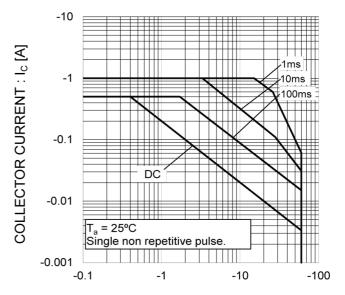
COLLECTOR OUTPUT CAPACITANCE : C_{ob} [pF]

● Electrical characteristic curves(T_a = 25°C)

Fig.9 Emitter Input Capacitance vs.
Emitter-Base Voltage
Collector Output Capacitance vs.
Collector-Base Voltage

Fig.10 Safe Operating Area

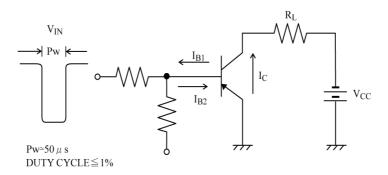


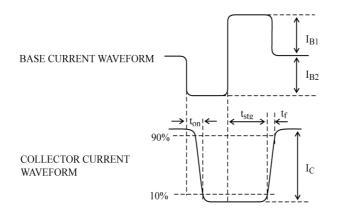


COLLECTOR-BASE VOLTAGE : V_{CB} [V]

COLLECTOR TO EMITTER VOLTAGE: V_{CE} [V]

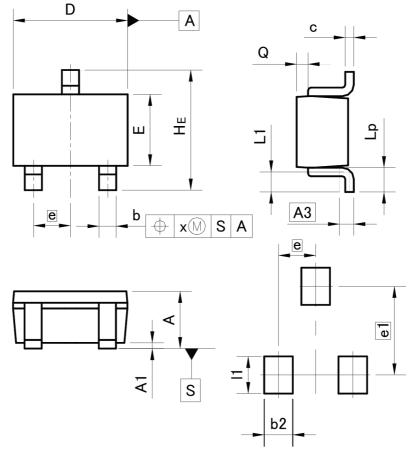
SWITCHING TIME TEST CIRCUIT





Dimensions

UMT3



Pattern of terminal position areas [Not a recommended pattern of soldering pads]

DIM	MILIM	ETERS	INCHES		
DIIN	MIN	MAX	MIN	MAX	
Α	0.80	1.00	0.031	0.039	
A1	0.00	0.10	0.000	0.004	
A3	0.5	0.25		10	
b	0.15	0.30	0.006	0.012	
С	0.10	0.20	0.004	0.008	
D	1.90	2.10	0.075	0.083	
E	1.15	1.35	0.045	0.053	
е	0.0	65	0.026		
HE	2.00	2.20	0.079	0.087	
L1	0.20	0.50	0.008	0.020	
Lp	0.25	0.55	0.010	0.022	
Q	0.10	0.30	0.004	0.012	
х	_	0.10	1	0.004	

DIM	MILIM	ETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
b2	_	0.50	-	0.020	
e1	1.55		0.0	61	
11	_	0.65	_	0.026	

Dimension in mm/inches



Notes

- 1) The information contained herein is subject to change without notice.
- 2) Before you use our Products, please contact our sales representative and verify the latest specifica-
- 3) Although ROHM is continuously working to improve product reliability and quality, semiconductors can break down and malfunction due to various factors.

 Therefore, in order to prevent personal injury or fire arising from failure, please take safety measures such as complying with the derating characteristics, implementing redundant and fire prevention designs, and utilizing backups and fail-safe procedures. ROHM shall have no responsibility for any damages arising out of the use of our Poducts beyond the rating specified by ROHM
- 4) Examples of application circuits, circuit constants and any other information contained herein are provided only to illustrate the standard usage and operations of the Products. The peripheral conditions must be taken into account when designing circuits for mass production.
- 5) The technical information specified herein is intended only to show the typical functions of and examples of application circuits for the Products. ROHM does not grant you, explicitly or implicitly, any license to use or exercise intellectual property or other rights held by ROHM or any other parties. ROHM shall have no responsibility whatsoever for any dispute arising out of the use of such technical information.
- 6) The Products are intended for use in general electronic equipment (i.e. AV/OA devices, communication, consumer systems, gaming/entertainment sets) as well as the applications indicated in this document.
- 7) The Products specified in this document are not designed to be radiation tolerant.
- 8) For use of our Products in applications requiring a high degree of reliability (as exemplified below), please contact and consult with a ROHM representative: transportation equipment (i.e. cars, ships, trains), primary communication equipment, traffic lights, fire/crime prevention, safety equipment, medical systems, servers, solar cells, and power transmission systems.
- Do not use our Products in applications requiring extremely high reliability, such as aerospace equipment, nuclear power control systems, and submarine repeaters.
- 10) ROHM shall have no responsibility for any damages or injury arising from non-compliance with the recommended usage conditions and specifications contained herein.
- 11) ROHM has used reasonable care to ensur the accuracy of the information contained in this document. However, ROHM does not warrants that such information is error-free, and ROHM shall have no responsibility for any damages arising from any inaccuracy or misprint of such information.
- 12) Please use the Products in accordance with any applicable environmental laws and regulations, such as the RoHS Directive. For more details, including RoHS compatibility, please contact a ROHM sales office. ROHM shall have no responsibility for any damages or losses resulting non-compliance with any applicable laws or regulations.
- 13) When providing our Products and technologies contained in this document to other countries, you must abide by the procedures and provisions stipulated in all applicable export laws and regulations, including without limitation the US Export Administration Regulations and the Foreign Exchange and Foreign Trade Act.
- 14) This document, in part or in whole, may not be reprinted or reproduced without prior consent of ROHM.



Thank you for your accessing to ROHM product informations.

More detail product informations and catalogs are available, please contact us.

ROHM Customer Support System

http://www.rohm.com/contact/